Erratum: "Electrical characteristics of lateral poly-silicon field emission triode using LOCOS process"

[J. Korean Vac. Sci. Tech. Vol. 3, No. 1, 40 (1999)]

Jae-Hoon Lee, Myoung-Bok Lee, Dong-Il Park, Sung-Ho Ham,* Jong-Hyun Lee, and Jung-Hee Lee

*School of Electronic and Electrical Engineering, *Sensor Technology Research Center, Kyungpook National University*

Due to a production error, Fig. 3 on p. 40 appeared incorrectly; the correct figure is:

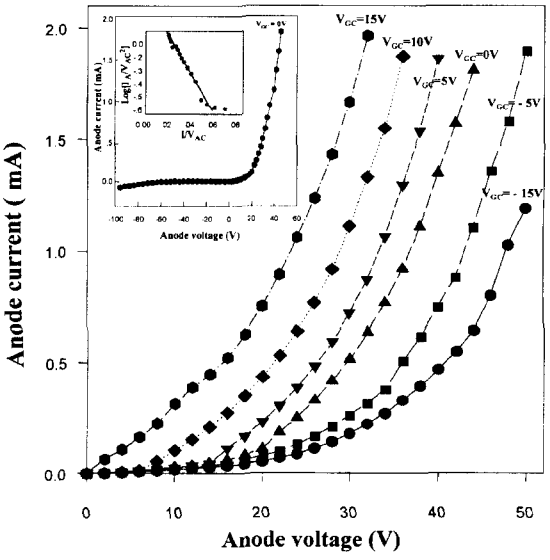

Fig. 3. Anode I-V characteristics of the field emission triodes in the normal operation mode, Insert : anode I-V characteristics for VGC = 0 V and the corresponding Fowler-Nordheim plot.

Instructions for JKVST Contributors

Contributors are strongly encouraged to prepare manuscript using MS-word or HWP for prompt publication. Contributors who need to utilize other word-processor must refer the editorial office of KVS prior to submission.

1. For the initial submission of the papers, one original and two copies of manuscript must be mailed to the Editor of the Korean Vacuum Society, *RM 805, the Korea Science and Technology Center, 635-4, Yeogsam-dong, Kangnam-ku, Seoul 135-703, Korea.* At this time, the cover letter, the original figure, and the manuscript diskette describing the employed word-processor on the label should be included.
   The Detailed information on galley proofs, publication charge, and copyright transfer will be mailed to the corresponding author of the peer-reviewed and accepted papers.
2. Authors can choose one of the following publications: full papers, letters, brief reports, shop-notes, and comments.
3. The full papers should be as concise as possible. The KVS recommends the general format and style only for full papers, e.g., abstract, introduction, experiment (optional), results and discussion, and summary (or conclusions). Others are authors' optional format.
4. Letters section is provided for important and current issues needing prompt publication. The maximum available space is four journal pages.
   Brief reports section is provided for pioneering discovery. The maximum available space is two journal pages.
   Shop-notes section is provided for new instrumental development of vacuum-related technique. The maximum available space is two pages.
   Comments section is provided for reader's comment. The maximum available space is two journal pages.
5. The manuscript should contain name and address of the author's institution, the corresponding author name, key words less than 10, the list of references, and the list of the figure captions.
6. The text must be neatly typed, double-spaced on A4-sized paper (21.0 cm × 29.7 cm) with 2.5 cm margins.
7. Equations should be neatly typed or written in ink and numbered on the right. For example;

For the *I-V* curve,

$$J_F = J_S \exp\left(\frac{qV_F}{nkT}\right), \text{ when } qV_F > 3kT \quad (1)$$

and

$$\Phi_{BN} = \frac{kT}{q} \ln\left(\frac{A^* T^2}{J_S}\right), \quad (2)$$

where J_S is the saturation current density, n the ideality factor, and A* the effective Richardson constant (8.16 $cm^{-2} \cdot K^{-2}$).

8. Literature references should be indicated by numbers in parentheses in the text, and the full references should be given in a separate list at the end of the manuscript. For example;

> Based on the electronegativity values of Ga, As, and Se given as 1.82, 2.20, and 2.48, respectively [1], Ohno and Shiraishi assigned the peak as originating from an As-Se peak with a slight formal positive charge localized on the As atom [2].
> .
> .
> .
> References
> [1] L. Pauling, *The Nature of the chemical Bond*, 3rd. ed. (Cornell University Press, Ithaca, 1960), pp. 101-107.
> [2] T. Ohno and K. Shiraishi, Phys. Rev. B **42**, 11194 (1990).

9. Tables and figures should be numbered respectively in the order in which they are referred in the text. Their suitable captions should make readers intelligible without reference to the text. Note approximate locations of the figures and tables in the margin of the text. For example;

Table 1. Optimal Ga-S and As-S bond length and energy on the GaAs(111) surface with an adsorbed S monolayer in the on-top and exchange sites.

Adsorption site	Bond	Length (nm)	Energy (eV)
on-top (-As≡Ga-S)	Ga-S	0.211	4.02
exchange (-As≡S)	As-S	0.240	4.32

10. Each figure should appear on a separate page. Drawings should be neatly prepared in india ink. The lettering in the figure should be sufficiently large and bold enough to permit the reduction in the actual publication. Figures should be identified in the margin with the author's name and figure number.